

FEATURES

- 6.40–7.20GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 9.5 dB Power Gain at 1dB Compression
- 36% Power Added Efficiency
- -46 dBc IM3 at PO = 25.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 6.40\text{-}7.20\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1100\text{mA}$	35.5	36.5		dBm
G_{1dB}	Gain at 1dB Compression $f = 6.40\text{-}7.20\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1100\text{mA}$	8.5	9.5		dB
ΔG	Gain Flatness $f = 6.40\text{-}7.20\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1100\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1100\text{mA}$ $f = 6.40\text{-}7.20\text{GHz}$		36		%
I_{d1dB}	Drain Current at 1dB Compression $f = 6.40\text{-}7.20\text{GHz}$		1100	1300	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10\text{ MHz}$ 2-Tone Test; $P_{out} = 25.5\text{ dBm S.C.L.}^2$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 65\% IDSS$ $f = 7.20\text{GHz}$	-43	-46		dBc
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}$, $V_{GS} = 0\text{ V}$		2000	2500	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}$, $I_{DS} = 20\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		5.5	6.0	$^\circ\text{C/W}$

Note: 1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	15V	10V
V_{gs}	Gate-Source Voltage	-5V	-4V
I_{gf}	Forward Gate Current	48mA	14.4mA
I_{gr}	Reverse Gate Current	-9.6mA	-2.4mA
P_{in}	Input Power	36dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175C	175C
T_{stg}	Storage Temperature	-65C to +175C	-65C to +175C
P_t	Total Power Dissipation	25W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

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EIC6472-4

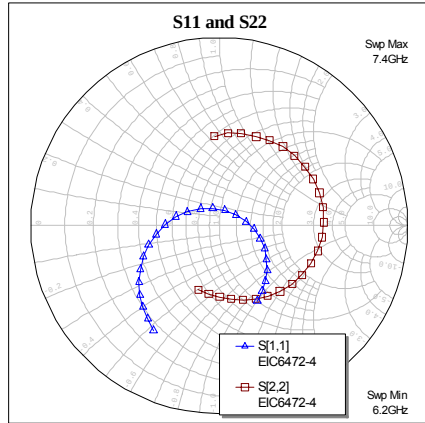
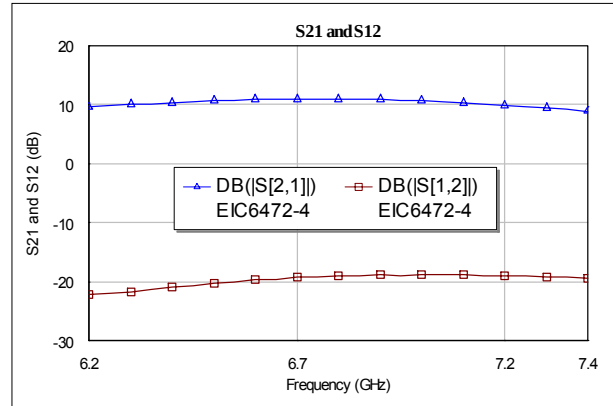
UPDATED 08/21/2007

6.40-7.20GHz 4-Watt Internally-Matched Power FET

PERFORMANCE DATA

Typical S-Parameters (T= 25°C, 50Ω system, de-embedded to edge of package)

$V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1100\text{mA}$



FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6.0	0.7446	-102.56	2.6955	-4.96	0.0623	-61.34	0.4238	127.4
6.2	0.6564	-122.03	3.0007	-31.42	0.0778	-87.4	0.4753	93.04
6.4	0.5197	-144.79	3.2845	-59.46	0.091	-116.15	0.5273	59.7
6.6	0.3381	-172.19	3.4917	-89.7	0.1042	-146.01	0.5579	26.43
6.8	0.1334	137.99	3.545	-121.42	0.1132	-176.76	0.5493	-6.3
7.0	0.1434	8.46	3.3891	-152.94	0.1165	153.37	0.4955	-38.82
7.2	0.3102	-35.87	3.1032	176.54	0.1127	123.35	0.4145	-72.21
7.4	0.4488	-63.26	2.7841	148.43	0.1073	94.96	0.3577	-108.03
7.6	0.5418	-88.96	2.4831	120.54	0.0965	66.98	0.3552	-148.1
7.8	0.5851	-112.49	2.1721	93.7	0.0875	40.86	0.4007	176.95
8.0	0.6041	-135.73	1.8779	68.06	0.0765	17.11	0.4693	151.21

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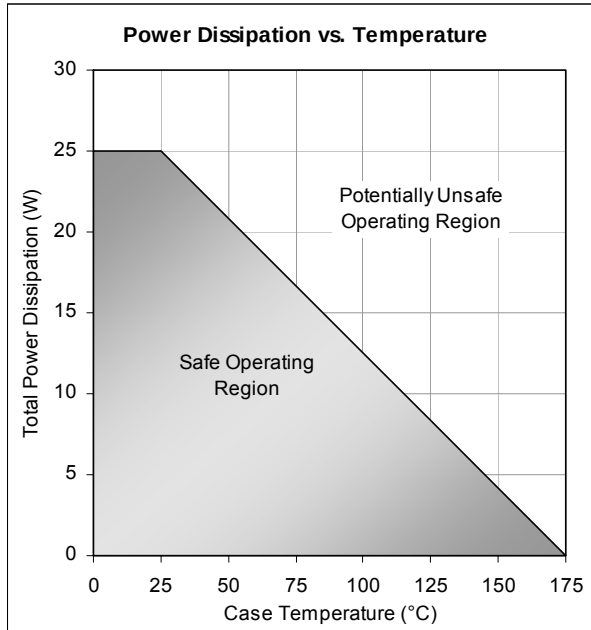
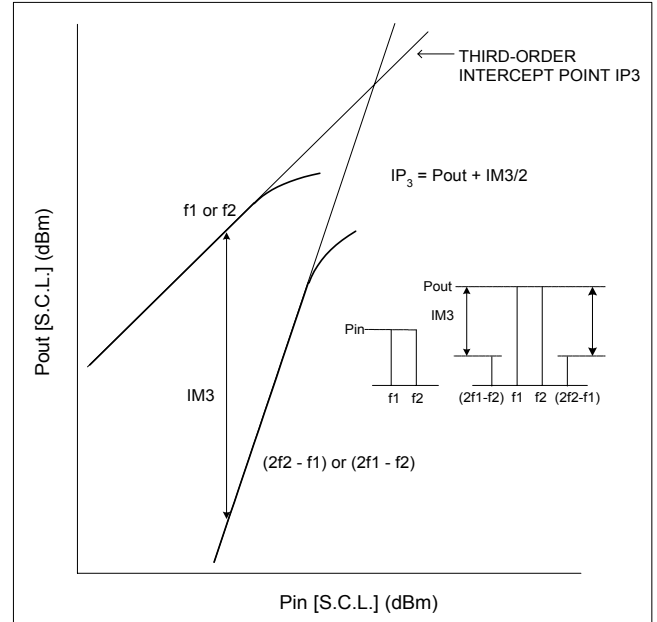


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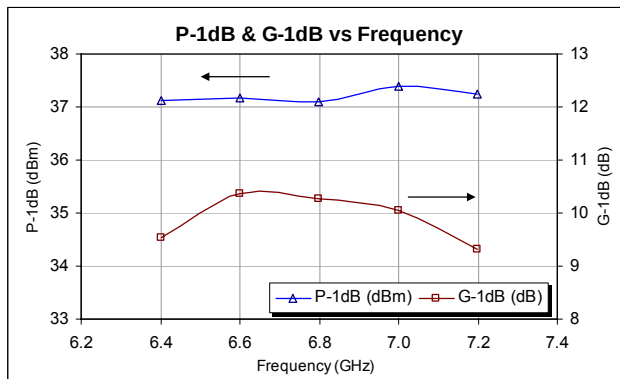
UPDATED 08/21/2007

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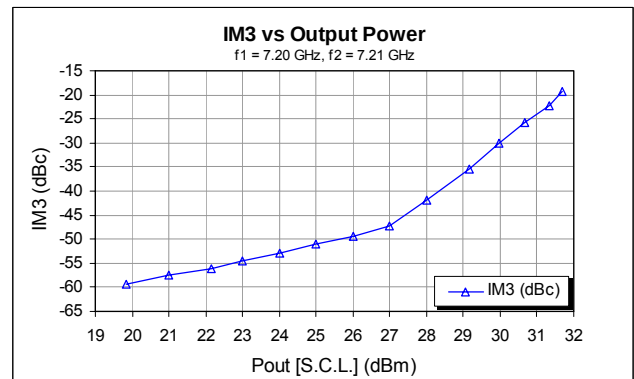
Power De-rating Curve and IM3 Definition



Typical Power Data ($V_{DS} = 10\text{ V}$, $I_{DSQ} = 1100\text{ mA}$)



Typical IM3 Data ($V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 65\% IDSS$)



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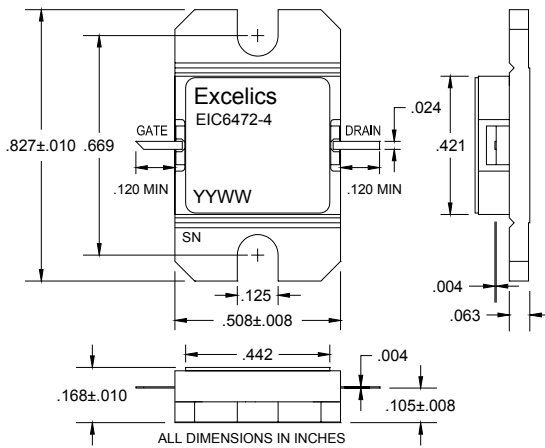
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PACKAGES OUTLINE

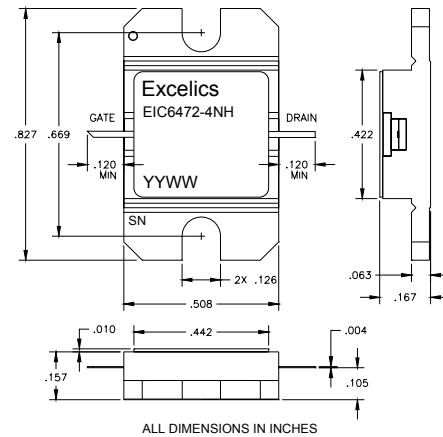
Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

EIC6472-4 (Hermetic)



Caution! ESD sensitive device.

EIC6472-4NH (Non-Hermetic)



Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC6472-4	Hermetic	Industrial	6.40-7.20GHz	35.5	-43
EIC6472-4NH	Non-Hermetic	Industrial	6.40-7.20GHz	35.5	-43

Notes: 1. Contact factory for military and hi-rel grades.
2. Exact test conditions are specified in "Electrical Characteristics" table.

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